

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
-30V	45mΩ@-10V	-4.1A
	65mΩ@-4.5V	

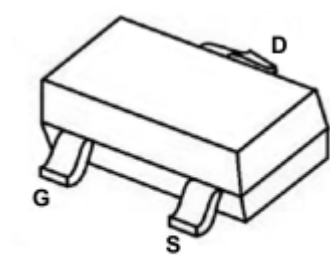
## Feature

- TrenchFET Power MOSFET
- Excellent  $R_{DS(on)}$  and Low Gate Charge

## Applications

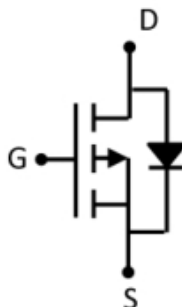
- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

## Package

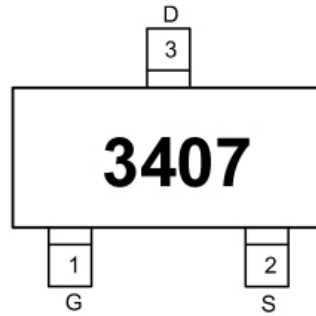


**SOT-23-3L**

## Circuit diagram



## Marking



## Absolute maximum ratings

( $T_a=25^{\circ}\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	-4.1	A
Power Dissipation	$P_D$	1.4	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	90	$^{\circ}\text{C}/\text{W}$
Junction Temperature	$T_J$	150	
Storage Temperature	$T_{STG}$	-55~ +150	$^{\circ}\text{C}$

## Electrical characteristics

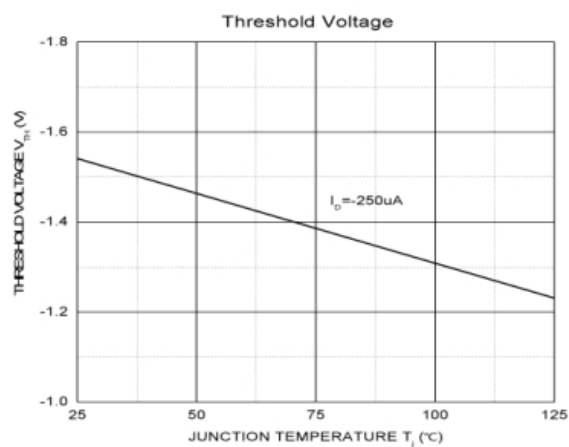
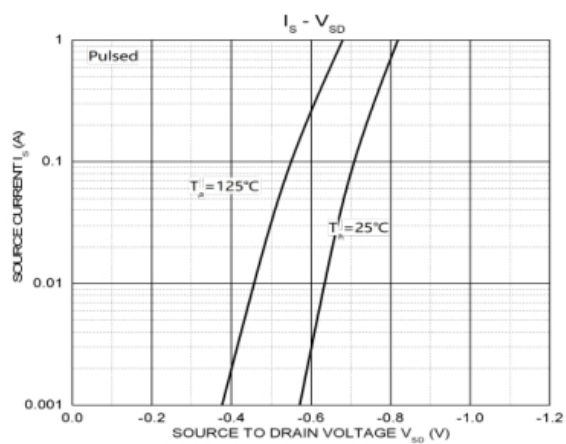
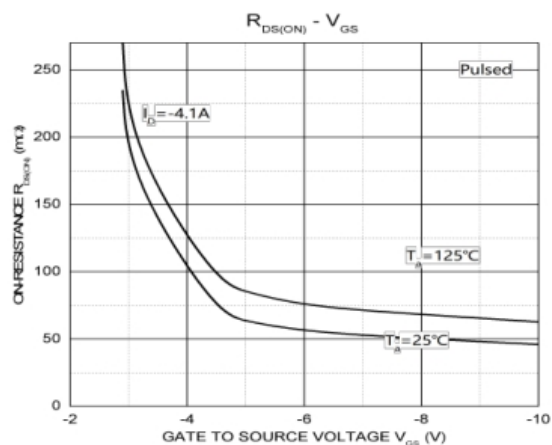
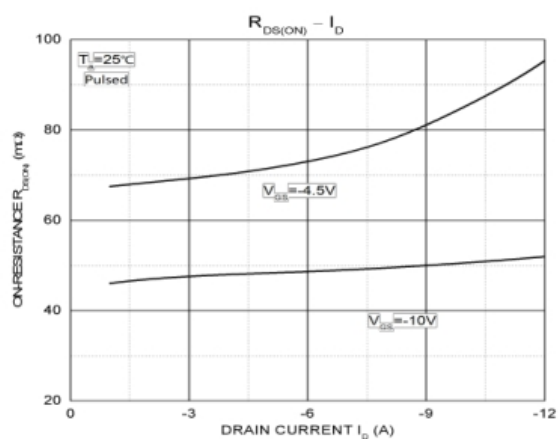
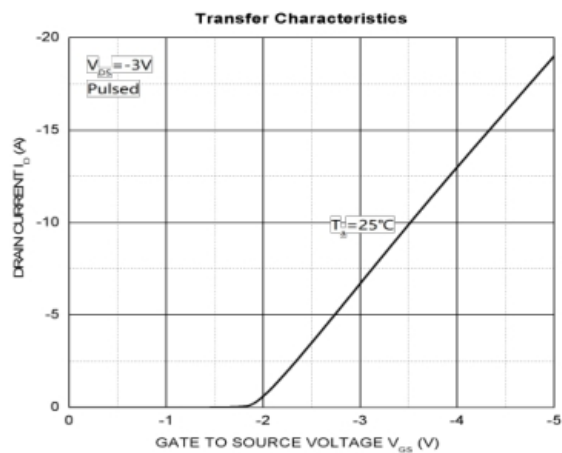
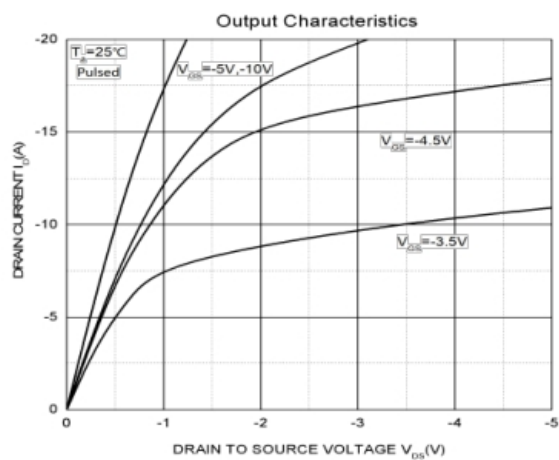
( $T_A=25^{\circ}\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV (BR)DSS	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-30			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V			-1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	μA
Gate threshold voltage <sup>1)</sup>	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1	-1.6	-2.5	V
Drain-source on-resistance <sup>1)</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.1A		45	60	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3A		65	90	
Forward transconductance <sup>1)</sup>	g <sub>FS</sub>	V <sub>DS</sub> = -5V, I <sub>D</sub> = -4A		10		S
Dynamic Characteristics <sup>(4)</sup>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> =0V, f=1MHz		700		pF
Output capacitance	C <sub>oss</sub>			120		
Reverse transfer capacitance	C <sub>rss</sub>			75		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.1A		13		nC
Gate-Source Charge	Q <sub>gs</sub>			3		
Gate-Drain Charge	Q <sub>gd</sub>			3		
Turn-on Delay Time	T <sub>d(on)</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> =-10V, R <sub>L</sub> =3.6Ω, R <sub>GEN</sub> =3Ω		8.6		nS
Turn-on Rise Time	T <sub>r</sub>			5.0		
Turn-Off Delay Time	T <sub>d(off)</sub>			28.2		
Turn-Off Fall Time	t <sub>f</sub>			13.5		
Source-Drain Diode Characteristics						
Diode Forward voltage	V <sub>DS</sub>	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V			-1.2	V

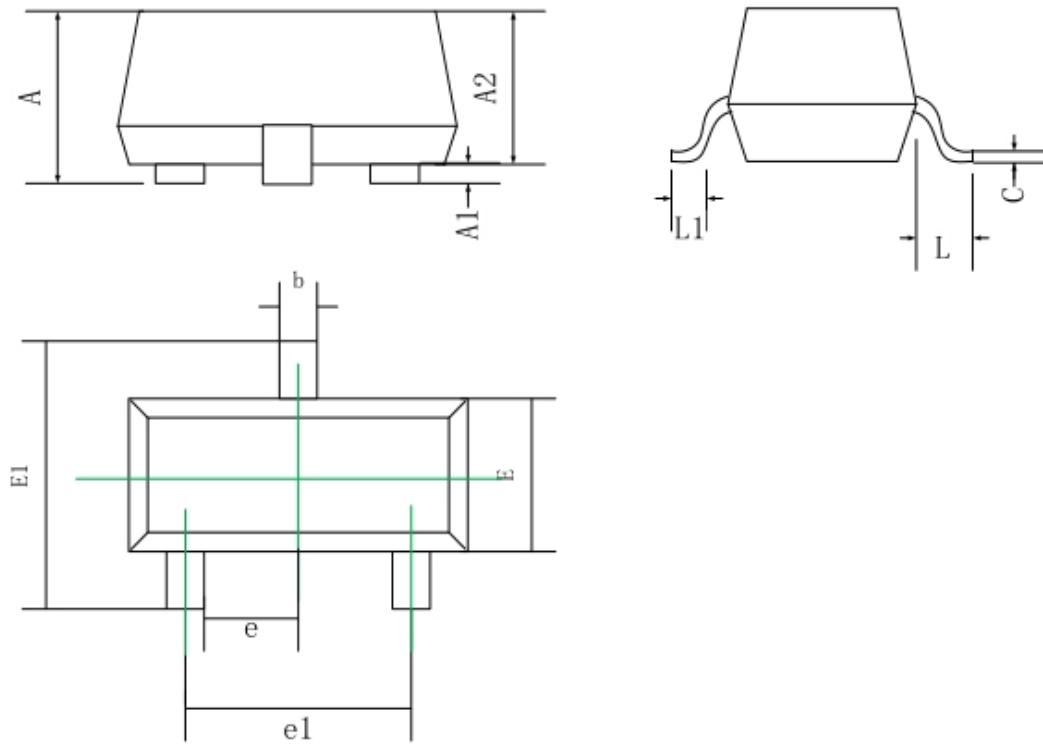
### Notes:

1. Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
2. These parameters have no way to verify.

## Typical Characteristics



## SOT-23-3L Package Information



Symbol	Dimensions in millimeters	
	Min.	Max.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.820	3.020
E	1.500	1.700
E1	2.650	2.950
e	0.950 Typ.	
e1	1.800	2.000
L	0.300	0.600
θ	0°	8°